

**REMARKS**

Applicant submits herewith a preliminary amendment with new claims to be entered in the application. The amendments to the specification at pages 6 and 14, are clarifying only. No new matter is added.

The amendments clarify that replenishment of the low aspect ratio crucible, while maintaining an optimal thermal gradient across the melt and particularly at the melt crystal interface, enables the resistivity or conductivity in the growing ingot to be substantially uniform in the axial (longitudinal) and radial dimensions.

Support for the amendments is found in claim 4 as originally filed, which specifies: "means for adding dopant as needed to the pre melter during crystal growth to provide compensation for segregation and establish a substantially uniform dopant concentration in the grown crystal." (Emphasis added.)

Support for the amendments is also found in the specification as filed at page 15, lines 3-5, which provides:

"...the axial resistance of the crystal can be better controlled as dopant can be added during recharging. This advantageously eliminates the axial resistivity gradient exhibited in crystals grown by the conventional CZ process. The effects of segregation in the melt and resulting non-uniform dopant profiles in the crystal are substantially eliminated." (Emphasis added.)

Applicant respectfully requests entry of the amendments in as much as they are clarifying only, are fully supported, and do not add new matter.

If necessary, the Commissioner is hereby authorized to charge payment or credit any overpayment to Deposit Account No. 501866 for any fees required.

Dated: March 18, 2005

Respectfully submitted,



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